			f 11	Time stand
L Number		deard. Text	IB	•
1		hardmark of "hard mark" of Fill of "silion nitride" same Ab 1 antirellect of "anti-reflective coathy".	USTAT; EF:///IF:/ IBM TLB	12 (1) Skol a (1 a 1 Het 2 +
	. 7.4	antifelled of antifelledite of the hardmask of "hard mass" of Fill 1 "silion nitride" osame APC of antireflect of "anti reflective coating" osame etch\$:	USFAT: EF./ OF./ IBM_TDB	2003/04/24 94:0/
	liser	resist of photoresist of pattern of patterned of patterned of patterning space (ARC) of antireflect of "antireflective coating"	USPAT; EFL; JF ; IBM TDB	114 (32),4 (14) 3 931,5
4	6 , C, 4	resist i photoresist i pattern i pattern i patterned or patterning with APC i antireflect or "anti reflective clating"	USPĀT; EPG; JPG; IBM TDB	21930494 99:3:
r.	ਬੁਝਵੰ	coresist or photoresist or pattern or patterned or patterning) with (APC or antireflect or "anti reflective")	USPAT; EFC; JPO; IBM_TDB	2003/04/14 10:19
<i>;</i>	192	coating"): same etch\$3 chardmask or "hard mask" or SiN or "silicon nitride": same collesist or photoresist or pattern or patterned or latterning with APO reantifetter or "anti reflective coating" same etch\$3	USPAT; EPO; JFO; IBM TDB	0003/04/14 00:35
	<u>; _ 13</u>	resist a photoresist or pattern or patterned or patterning with APC i antireflect or "anti reflective duating" same etch\$2 and 458/\$.c.ls.	USPAT; EPO; JPO; IBM_TDB	0003704714 09:53
٢		<pre>-hardmask or "hard mask" or SiN or "silicon nitride": with (APC or antireflect or "anti reflective coating")</pre>	USPAT; EPC; JPU; IBM_TDB	21.3794.14 99:17
c,	234	Tresist or photoresist or pattern - 1 patterned or patterning same - hardmask or "hard mask" or SiN or "silicon nitride" with TAPC or antireflect or "anti reflective coating":	USPĀT; EPC; JPC; IBM_TDB	2018/04/14 09:19
10	4672	<pre>pattern or patterned or patterning- with (ARC or antireflect or "anti- reflective coating";</pre>	USPAT; EFO; JPO; IBM TDB	2003/04/14 09:52
11	481	: pattern or patterned or patterning: with (ARC or antireflect or "antireflective coating": with (opening or Via or contact)	USPĀT; EPO; JPC; IBM_TDB	2003/34/14 09:51
10	1209	pattern or patterned or patterning same APC or antireflect or "anti- reflective coating" same presist or	USPAT; EPC; JPO; IBM_TDP	2003/04/14 09:53
: •	१५७	photoresist pattern i patterned i patterning with API i antireflect i "anti reflective pating" with resist i photoresist	MSFAT; EFT; IF.; IBM _U TDB	24 3474744 1.:24
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·		<pre>pening of contact scales AFT d antifering to a "anti-deficitive scales AFT" and FAF</pre>	EE / TE /	
10		<pre>penind is distant with AFT 1 antireflect in "anti reflective clating" in BAPU</pre>	WEAT; EF ; MEC; IRM_TUB	
	2.50	<pre>c. grening i centa to with APS d captiretlest i "anti-fellestive stating" ci FAFS common et d2;</pre>	MSFĀT; EFP; MEJ; IBM TIB	
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